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[54] PROCESS FOR THE PRODUCTION OF ACCELEROMETERS USING SILICON ON INSULATOR TECHNOLOGY

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257/418 437/901, 89; 216/2; 257/254, 417, 418;

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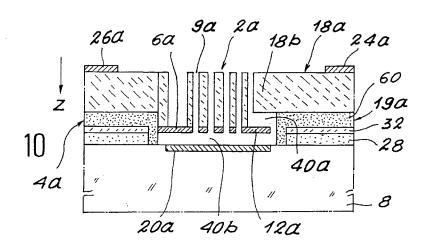
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[57] **ABSTRACT**

A process for the production of accelerometers using the silicon on insulator method. The process comprises the following stages: a) producing a conductive monocrystalline silicon film on a silicon substrate and separated from the latter by an insulating layer; b) etching the silicon film and the insulating layer up to the substrate in order to fix the shape of the mobile elements and the measuring devices; c) producing electric contacts for the measuring devices; d) partial elimination of the insulating layer in order to free the mobile elements, the remainder of the insulating layer rendering integral the substrate and the moving elements.

17 Claims, 7 Drawing Sheets



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